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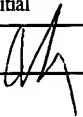
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

Sheet 1 of 1

(Rev. 5/92) Comparable to Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	Atty. Docket No. 86397	Serial No. not yet assigned
	Applicants Satoshi Komiya et al.	
	Filing Date: herewith	Group

U.S. PATENT DOCUMENTS


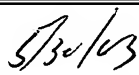
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	5,935,320	08/10/1999	GRAEF ET AL.			

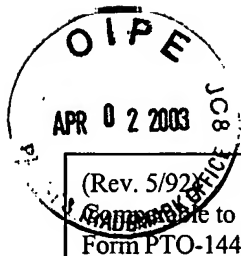
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	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	11135514A	21.05.1999	JP			ABS	
	10098047A	14.04.1998	JP			ABS	
	61193456A	27.08.1986	JP			ABS	
	10208987A	18.04.200	JP			ABS	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	International Search Report (date of mailing 24.10..2000) which issued in connection with above cited references

Examiner 	Date Considered 
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	



(Rev. 5/92) Patent Office to Form PTO-1449 INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 86397	Serial No. 10/049,875
	Applicants Satoshi Komiya et al.		
	Filing Date February 12, 2002	Group Unassigned	

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*Ex. Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

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	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
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	B2	0 962 556 A1	12/08/1999	Europe	C30B	15/00	X

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	C1	Shimura et al.; "Nitrogen Effect on Oxygen Precipitation in Czochralski Silicon," 320 <i>Applied Physics Letters</i> , Vol. 48(3), January 1986, New York, USA, 3 pgs. (XP-002105443)
	C2	Ciszek et al.; "Effect of Nitrogen Doping on Microdefects and Minority Charge Carrier Lifetime of High-Purity, Dislocation-Free and Multicrystalline Silicon," <i>Solar Energy Materials and Solar Cells</i> , Vol. 41/42, 1996, pp. 61-70 (XP 000614222)
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Examiner 	Date Considered
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	